

Exact result on the Mott transition in a two-dimensional model  
of strongly correlated electrons

Frédéric Mila

*Laboratoire de Physique Quantique*

*Université Paul Sabatier*

*31062 Toulouse Cedex*

*France*

We study the properties of a quarter-filled system of electrons on a square lattice interacting through a local repulsion  $U$  and a nearest-neighbour repulsion  $V$  in the limit  $V = +\infty$ . We identify the ground-state for  $U$  large enough and show that domain walls appear below a critical value  $U_c = 4t/\pi$ . We argue that this corresponds to a metal-insulator transition due to Mott localization.

A lot of attention is currently devoted to the problem of metal-insulator transitions (MIT) driven by correlations in electronic systems [1]. While this problem has some direct experimental relevance, the main reason for this renewed interest lies in the possibility that, on the metallic side of the transition, but close enough to the boundary, the electron gas might no longer behave as a Fermi liquid. The model most often considered to study this phenomenon is the Hubbard model defined by

$$H = -t \sum_{\langle ij \rangle, \sigma} (c_{i\sigma}^\dagger c_{j\sigma} + h.c.) + U \sum_i n_{i\uparrow} n_{i\downarrow} \quad (1)$$

where the symbol  $\langle ij \rangle$  means summation over pairs of nearest neighbours. At half-filling, this model is believed to undergo a transition from a metallic phase to an insulating one as  $U$  increases with a critical value of the repulsion  $U_c$  that depends on the lattice and on the dimension. The main source of concern in using this model to study Mott transitions is that the MIT that occurs is often due to the appearance of a spin-density wave (SDW) and not to Mott localisation as first pointed out by Slater [2]. This is in particular true for lattices that lead to perfect nesting, like e.g. the cubic lattice, in which case  $U_c = 0$ . This was confirmed by the Bethe ansatz solution of the one-dimensional Hubbard model by Lieb and Wu [3]. On the contrary, Mott localisation is expected to yield a finite value for  $U_c$ . In that respect, to identify models that exhibit a MIT due to Mott localisation is an important issue.

In this paper, we concentrate on the extended Hubbard model defined by

$$H = -t \sum_{\langle ij \rangle, \sigma} (c_{i\sigma}^\dagger c_{j\sigma} + h.c.) + U \sum_i n_{i\uparrow} n_{i\downarrow} + V \sum_{\langle ij \rangle} n_i n_j \quad (2)$$

on a square lattice at quarter-filling. The central motivation to study such an extension of the Hubbard model comes from the one-dimensional case which is known to have a MIT when  $U$  and  $V$  increase. The first result on that problem was obtained about 20 years ago by Ovchinnikov [4] who showed that when  $U = +\infty$  there is a MIT for  $V = 2t$ . Quite

$(+\infty, 2t)$ , which is nothing but Ovchinnikov's result, to  $(4t, +\infty)$ . The shape of the line was obtained numerically, but it was possible to prove analytically that the point  $U = 4t$ ,  $V = +\infty$  belongs to the boundary. That this transition is of the Mott type is quite clear for  $V = +\infty$  as there is a full spin degeneracy and hence no SDW in the insulating phase. In dimension 2, we expect to get rid of the SDW-driven transition because this model is not half-filled but quarter-filled, in which case there is no perfect nesting for the square lattice.

The essential reason that allowed an exact determination of  $U_c$  for  $V = +\infty$  in the one-dimensional case is in fact independent of the dimension and can be summarized as follows. A convenient way to take the fact that  $V$  is infinite into account is to include it as a constraint that restricts the Hilbert space to states with no pair of particles sitting next to each other. Then, it is easy to see that, for  $U$  large enough, the ground state is the checkerboard state obtained by putting one particle on each site of one sublattice and no particle on the other sublattice (see fig.1). This is an eigenstate because all the states that could be connected to it by the hopping term are not in the Hilbert space due to the constraint imposed by  $V = +\infty$ . Besides all the other states have at least one doubly occupied site and are certainly higher in energy when  $U$  is large enough. The crucial point is that this checkerboard state is always an eigenstate regardless of the value of  $U$  because of the constraint. However, when  $U$  decreases, it is no longer so costly to make local pairs, and states having such local pairs can be lower in energy than the checkerboard state due to a gain of kinetic energy.

There is an important difference however between the one-dimensional and two-dimensional cases. In 1D, a single vacancy is already a mobile defect: It splits into two doublets that can move away from each other [6]. In 2D, any defect made of a *finite* number of vacancies cannot move far away. To see this, consider a rectangle that encloses all the vacancies and whose sides go through empty sites of the checkerboard configuration (see fig.2). It is easy to see that all the particles located outside this rectangle are not able to

the particles outside the rectangle are either outside the rectangle or on its boundary, and they have at least two particles as neighbours.

So the only chance to get a metallic state, that is charge propagation, is to consider defects with an infinite number of vacancies. From what we just saw, these vacancies have to constitute a connected set in order to allow for charge propagation. The cheapest way in terms of the number of vacancies per unit length is, like in a ferromagnet, to make a domain wall between two checkerboard configurations translated from each other by one lattice spacing (see fig.3). Due to the constraint, one has to remove a row after performing the translation. So the density of vacancies per unit length in such a defect is equal to the density of particles in a row, that is  $1/2$ . To create a vacancy, one has to create a local pair somewhere else with an energy cost  $U$ . So the potential energy per unit length of such a domain wall is  $U/2$ .

Now, such a defect is able to gain kinetic energy. The elementary move is depicted in fig.3. Let us keep track of the position of the domain wall by drawing a line that joins the middles of two neighbouring empty sites. Let us also assume for the moment that one point is fixed. Taking that point as a reference, the position of the wall is determined by the succession of bonds going up or down. A move is possible only if two successive bonds are going in opposite ways, and it consists of exchanging them. If we represent a configuration by a series of 0 and 1, where 0 stands for a down-going bond and 1 for an up-going bond, a configuration on a periodic finite system has as many 0 as 1, and the elementary moves are  $01 \rightarrow 10$  and *vice versa*, with amplitude  $-t$ . This is equivalent to the eigenvalue problem of spinless fermions on a 1D chain at half-filling with amplitude  $-t$ . The kinetic energy per unit length is thus given by

$$\frac{1}{2\pi} \int_{-\pi/2}^{\pi/2} -2t \cos k \, dk = \frac{-2t}{\pi} \quad (3)$$

This mapping relies on the boundary condition that one point of the wall is fixed. In the

$U/2 - 2t/\pi$ . It vanishes at a critical value  $U_c = 4t/\pi$ . Below that value, domain walls are present in the ground-state.

The presence of domain walls in the ground-state does not guarantee by itself that the state is metallic. For instance, in the case of the weak-coupling Hubbard model, it is believed that the domain walls that appear away from half-filling crystallize, and that the system remains insulating up to a certain doping [7]. However, this effect is due to the large extension of the domain walls which gives rise to a long-range interaction between them. In the present case, the interaction between walls is local, and such a crystallization is unlikely to occur. So we believe that the appearance of domain walls in the ground-state corresponds to a metal-insulator transition. A more careful analysis of the interaction between domain walls is needed however to settle that issue. Concerning the nature of the transition, we note that, as in the 1D case, there is a full spin degeneracy in the insulating state, and hence no SDW. Thus the MIT cannot be due to a SDW and has to come from Mott localization. However, the insulating ground-state is a commensurate charge-density wave, so that the lattice translation symmetry is broken, in agreement with a general argument of Lee and Shankar [8].

Finally, let us comment on the possible applications of these results. This paper provides an example of Mott transition in dimension 2 for which the critical value of the interaction is known exactly. This might be useful to check approximate methods used in the context of Mott transitions. If one can extend the results to finite values of  $V$ , this model might also provide an example of Mott transition for reasonable values of  $U$  and  $V$  [9]. In that respect, we should note that similar results can be obtained for bosons. Charging effects in Josephson junction networks would then be a good realization of these ideas.

I acknowledge useful discussions with K. Penc, D. Poilblanc, S. Sorella, H. Tsunetsugu, T. Ziman and X. Zotos.

## REFERENCES

- [1] The original idea can be found in N. F. Mott, *Phil Mag* **6**, 287 (1961). Among the recent developements, let us mention the work in infinite dimension (see e.g. M. J. Rozenberg et al, *Phys Rev Lett* **69**, 1236 (1992), A. Georges and W. Krauth, *Phys Rev Lett* **69**, 1240 (1992), V. Janis and D. Vollhardt, *Int Journ Mod Phys B* **6**, 731 (1992) and M. Jarrell, *Phys Rev Lett* **69**, 168 (1992)). Another recent development of the field can be found in M. Imada, *J Phys Soc Japan* **62**, 1105 (1993). References to earlier work can be found in these papers.
- [2] J. C. Slater, *Phys Rev* **82**, 538 (1951).
- [3] E. H. Lieb and F. Y. Wu, *Phys. Rev. Lett.* **20**, 1445 (1968)
- [4] A. A. Ovchinnikov, *Sov Phys JETP* **37**, 176 (1973).
- [5] F. Mila and X. Zotos, *Europhys Lett* **24**, 133 (1993); K. Penc and F. Mila, *Phys. Rev. B*, in press.
- [6] M. Fowler and M. W. Puga, *Phys. Rev. B* **18**, 1 (1978).
- [7] D. Poilblanc and T. M. Rice, *Phys. Rev. B.* **39**, 9749 (1989); H. Schulz, *Phys. Rev. Lett.* **64**, 1445 (1990).
- [8] D. H. Lee and R. Shankar, *Phys. Rev. Lett.* **65**, 1490 (1990).
- [9] If  $V$  is large but finite, a magnetic coupling  $J_{eff}$  of order  $t^4/UV^2$  will appear due to superexchange, leading to antiferromagnetic order. However, this energy scale is much smaller than the charge gap, which is of order  $U$ , so that the insulating state can still be considered as a Mott insulator.

## FIGURES

FIG. 1. Checkerboard configuration. Crosses stand for electrons with spin up or down; small circles stand for empty sites.

FIG. 2. Example of a defect made of a few vacancies (heavy circles).

FIG. 3. Typical configurations of a domain wall. The dashed line corresponds to the new configuration obtained after an elementary move from the original one (solid line).